

# BRCS020N04RA

Rev.C Mar.-2023

## 描述 / Descriptions

TO-220 塑封封装 N 沟道场效应管。  
N-CHANNEL MOSFET in a TO-220 Plastic Package.

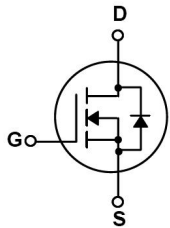
## 特征 / Features

低电阻,开关速度快,无卤产品。  
Ultra Low On-Resistance,fast switching, HF Product.

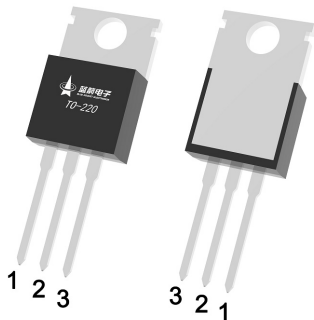
## 用途 / Applications

该器件适用于高效电源模块,主动式 PFC 电路和基于半桥拓扑结构的电子节能灯。  
These devices are well suited for high efficient switched mode power supplies, Active power factor correction, electronic lamp ballast based on half bridge topology.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : G      PIN 2、 4 : D      PIN 3 : S

## 印章代码 / Marking

见印章说明。 See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Drain Current	I <sub>D</sub> (Tc=25°C)	220	A
Pulsed Drain Current	I <sub>DM</sub>	800	A
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Single Pulsed Avalanche Energy L=0.5mH	E <sub>AS</sub>	482	mJ
Avalanche Current	I <sub>AS</sub>	35	A
Total Power Dissipation	P <sub>D</sub> (Tc=25°C)	187	W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C
Thermal Resistance-Junction to Ambient	t ≤ 10s	R <sub>θJA</sub>	15
	Steady-State		60
Thermal Resistance-Junction to Case	Steady-State	R <sub>θJC</sub>	0.67

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V	I <sub>D</sub> =250μA	40	44		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V	V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current Forward	I <sub>GSS</sub>	V <sub>GS</sub> =±20V	V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub>	I <sub>D</sub> =250μA	1	1.6	3	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V	I <sub>D</sub> =20A		1.6	2	mΩ
		V <sub>GS</sub> =4.5V	I <sub>D</sub> =10A		2.1	4	
Forward On Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V	I <sub>S</sub> =1A			1.2	V
Input Capacitance	C <sub>iSS</sub>	V <sub>DS</sub> =25V f=1MHz	V <sub>GS</sub> =0V		11000		pF
Output Capacitance	C <sub>oSS</sub>				840		
Reverse Transfer Capacitance	C <sub>rSS</sub>				650		

## 电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Gate resistance	$R_g$	$f=1\text{MHz}$		1.45		$\Omega$
Total Gate Charge	$Q_g(10\text{V})$	$V_{GS}=10\text{V}$ $V_{DS}=20\text{V}$ $I_D=20\text{A}$		68		nC
Total Gate Charge	$Q_g(4.5\text{V})$			28		
Gate Source Charge	$Q_{gs}$			16.5		
Gate Drain Charge	$Q_{gd}$			4.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}$ $V_{DS}=20\text{V}$ $R_L=1\Omega$ $R_{GEN}=3\Omega$		12.5		ns
Turn-On Rise Time	$t_r$			9.5		
Turn-Off Delay Time	$t_{d(off)}$			57.5		
Turn-Off Fall Time	$t_f$			10.5		

电参数曲线图 / Electrical Characteristic Curve

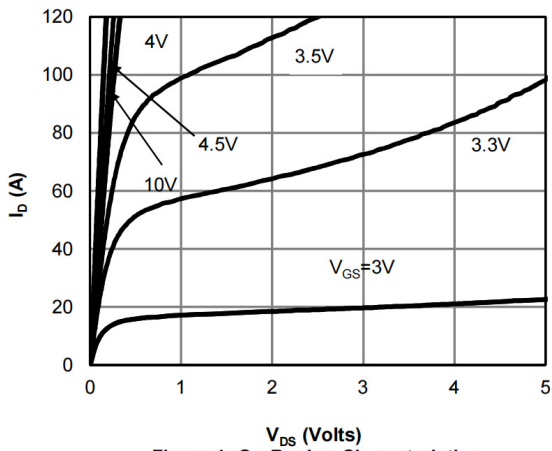


Figure 1: On-Region Characteristics

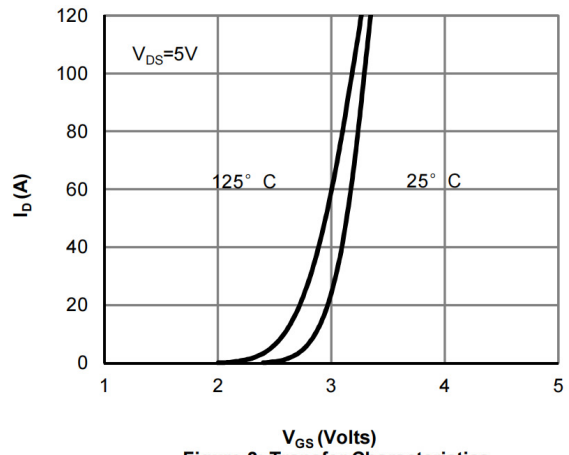


Figure 2: Transfer Characteristics

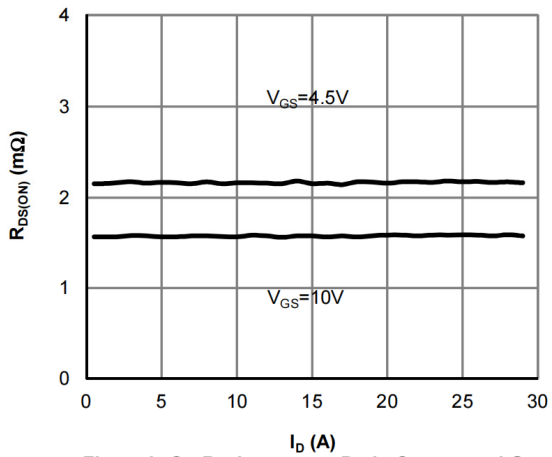


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

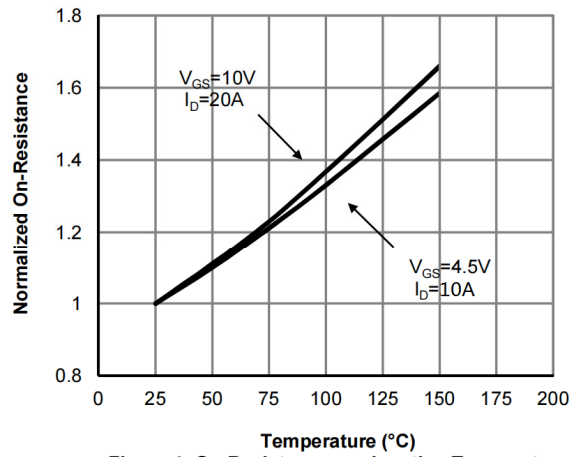


Figure 4: On-Resistance vs. Junction Temperature

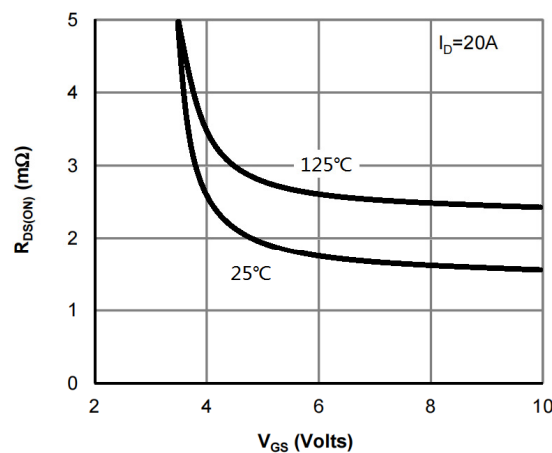


Figure 5: On-Resistance vs. Gate-Source Voltage

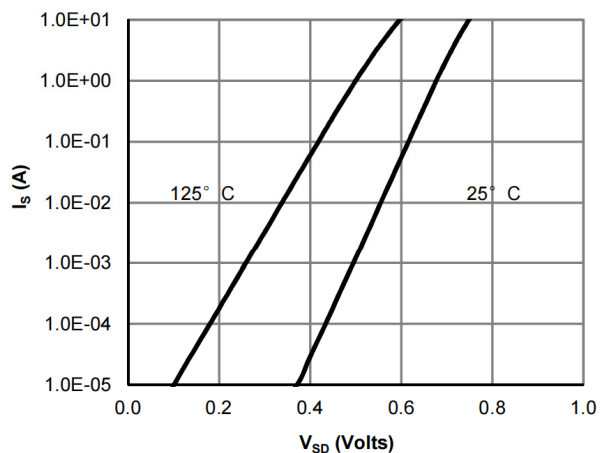
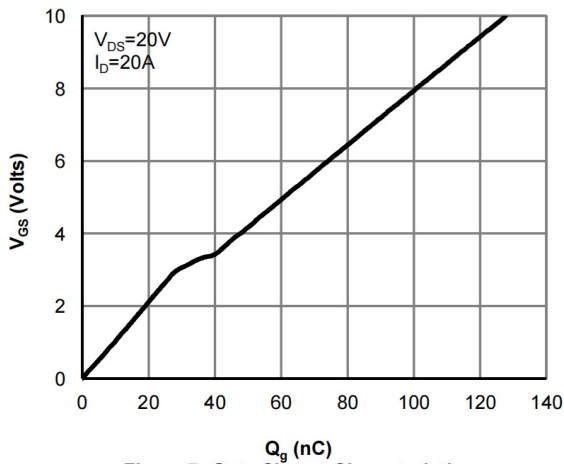
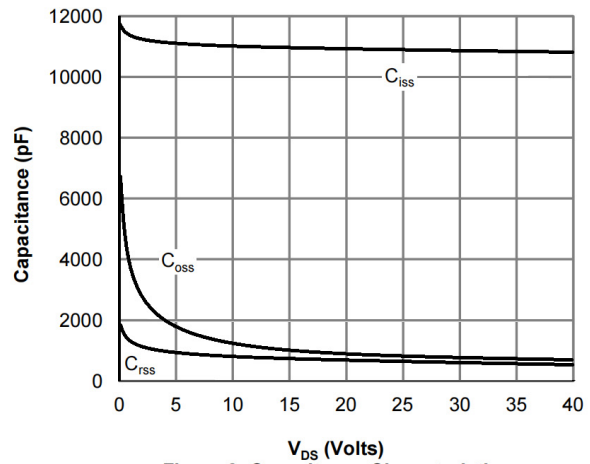


Figure 6: Body-Diode Characteristics

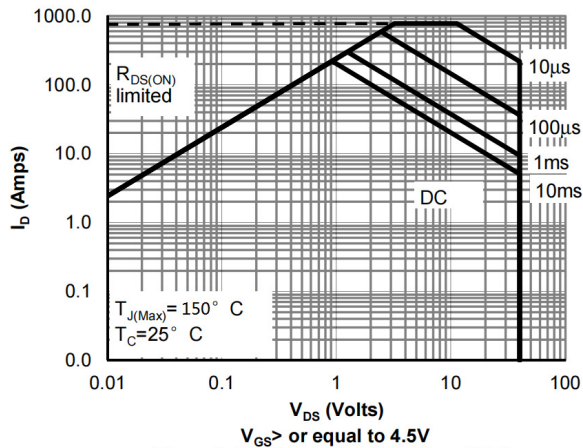
**电参数曲线图 / Electrical Characteristic Curve**



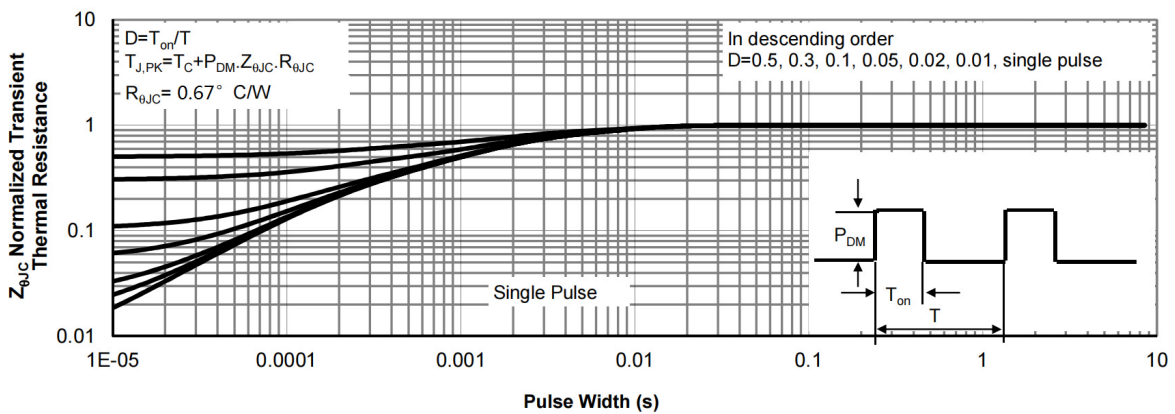
**Figure 7: Gate-Charge Characteristics**



**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area**

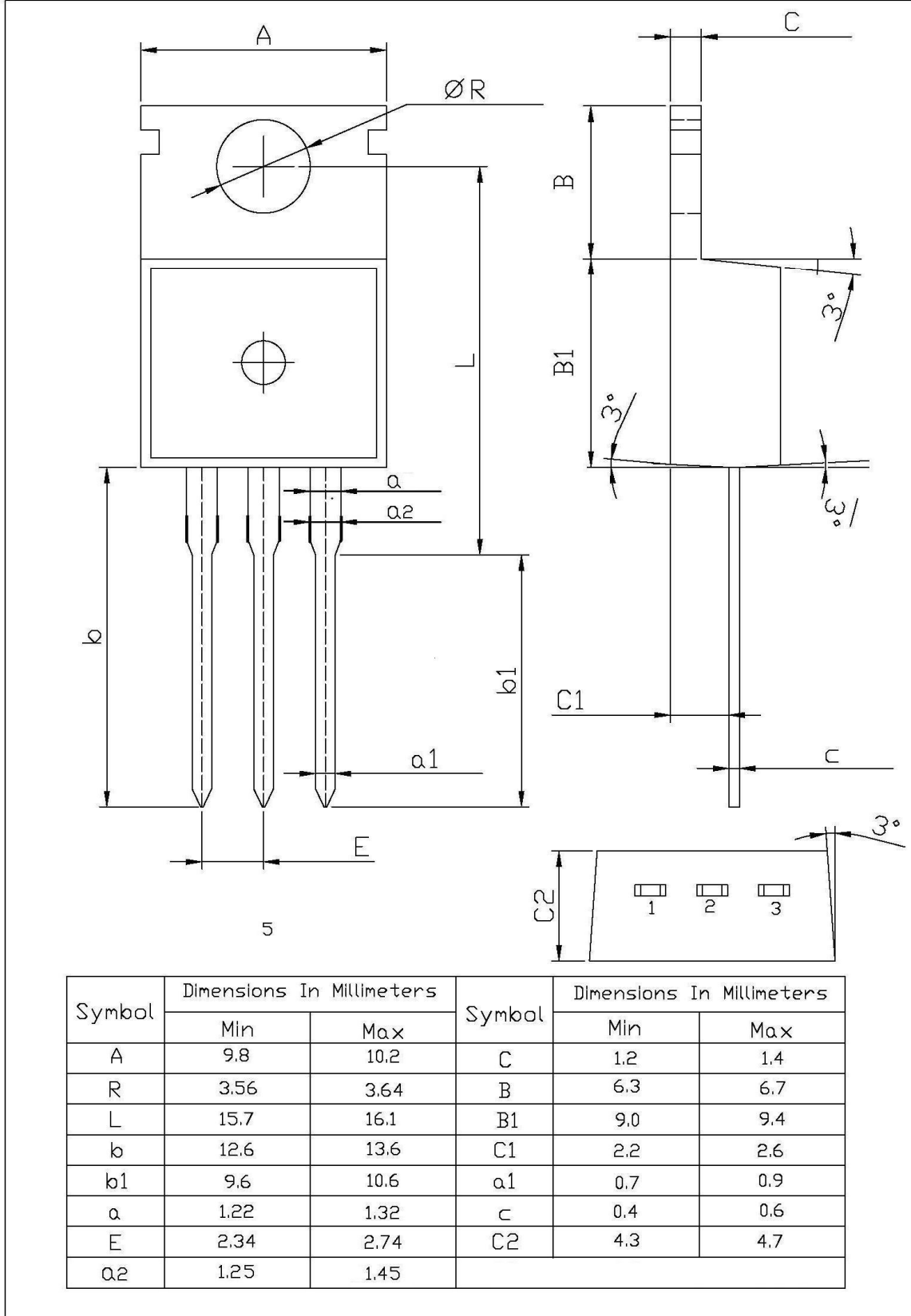


**Figure 10: Normalized Maximum Transient Thermal Impedance**

外形尺寸图 / Package Dimensions

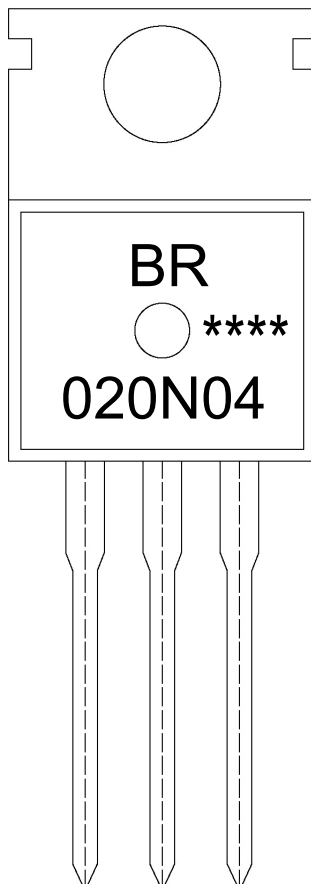
T0-220

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	9.8	10.2	C	1.2	1.4
R	3.56	3.64	B	6.3	6.7
L	15.7	16.1	B1	9.0	9.4
b	12.6	13.6	C1	2.2	2.6
b1	9.6	10.6	a1	0.7	0.9
a	1.22	1.32	c	0.4	0.6
E	2.34	2.74	C2	4.3	4.7
a2	1.25	1.45			

**印章说明 / Marking Instructions**



说明：

BR： 为公司代码

020N04： 为型号代码

\*\*\*\*： 为生产批号代码，随生产批号变化

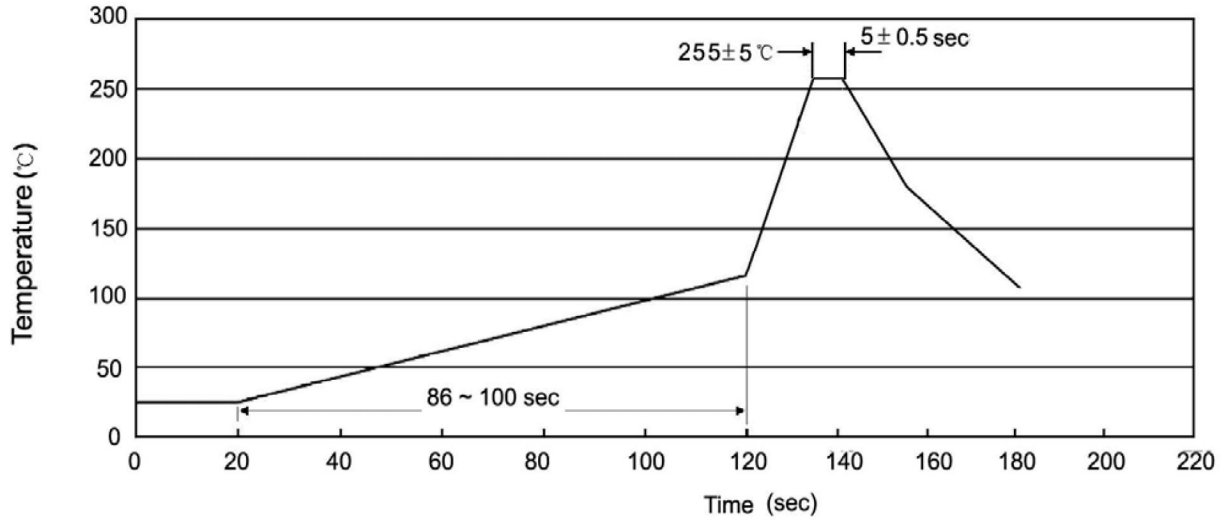
Note:

BR: Company Code

020N04: Product Type

\*\*\*\*: Lot No. Code, code change with Lot No

**波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)**



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：270±5°C      时间：10±1 sec.      Temp.:270±5°C      Time:10±1 sec

**包装规格 / Packaging SPEC.**

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

**使用说明 / Notices**